

ABSTRACT

A thin film transistor is provided that suppresses OFF current (photoconductive current) during light irradiation and that realizes high performance and high reliability. Specifically, there is provided a thin film transistor comprising a polycrystalline silicon semiconductor layer having formed therein a channel region, a source region, and a drain region, the source region and the drain region disposed on either side of the channel region. A depletion layer is formed between the channel region and the drain region. The width of the depletion layer and photoconductive current are in a proportional relationship, the photoconductive current generated when the channel region is irradiated with light, and the width of the depletion layer is equal to or less than a value obtained on the basis of the proportional relationship so that the photoconductive current falls within a range of specified permissible values.